**Vishay Semiconductors** 

# Hyperfast Rectifier, 60 A FRED Pt<sup>®</sup> Gen 5



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### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub> 60 A								
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	2.1 V							
t <sub>rr</sub>	30 ns							
T <sub>J</sub> max.	175 °C							
Package	TO-247AD 2L							
Circuit configuration	Single							

### **FEATURES**

- Hyperfast and optimized Q<sub>rr</sub>
- Best in class forward voltage drop and switching losses trade off
- · Optimized for high speed operation
- FREE • 175 °C maximum operating junction temperature
- Polyimide passivation
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

### **MECHANICAL DATA**

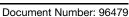
#### Case: TO-247AD 2L

Molding compound meets UL 94 V-0 flammability rating Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V					
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 105 °C, D = 0.50	60						
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 45 °C, $t_{p}$ = 10 ms, sine wave	420	A					
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 105 °C, D = 0.50, f = 20 kHz	120						
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C					

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX.									
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	1200	-	-				
Forward voltage	VF	I <sub>F</sub> = 60 A	-	2.6	3.15	V			
Forward voltage	۷F	I <sub>F</sub> = 60 A, T <sub>J</sub> = 125 °C	-	2.1	-				
Deverse leakerse eurrent	1	V <sub>R</sub> = V <sub>R</sub> rated	-	-	50				
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA			
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	32	-	pF			
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH			

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J$ = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		30	-			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	120	-	ns		
		T <sub>J</sub> = 125 °C		-	170	-			
Peak recovery current		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 40 A dI <sub>F</sub> /dt = 600 A/µs V <sub>R</sub> = 400 V	-	17	-	A		
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	32	-			
	0	T <sub>J</sub> = 25 °C		-	970	-	nC		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2950	-			
Deverse receiver time		T <sub>J</sub> = 25 °C		-	90	-	ns		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	130	-			
Deals receiver a current		T <sub>J</sub> = 25 °C	$I_{\rm F} = 60  {\rm A}$	-	32	-	A		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 1000 A/µs V <sub>B</sub> = 800 V	-	53	-			
	0	T <sub>J</sub> = 25 °C		-	1570	-	-0		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C	]	-	4300	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP.										
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	0.4	°C/W				
Weight			-	5.5	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C				
Marking device		Case style: TO-247AD 2L	E5PX6012L							

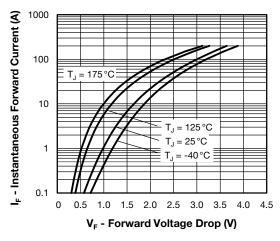
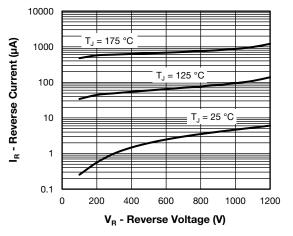
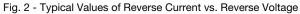


Fig. 1 - Typical Forward Voltage Drop Characteristics





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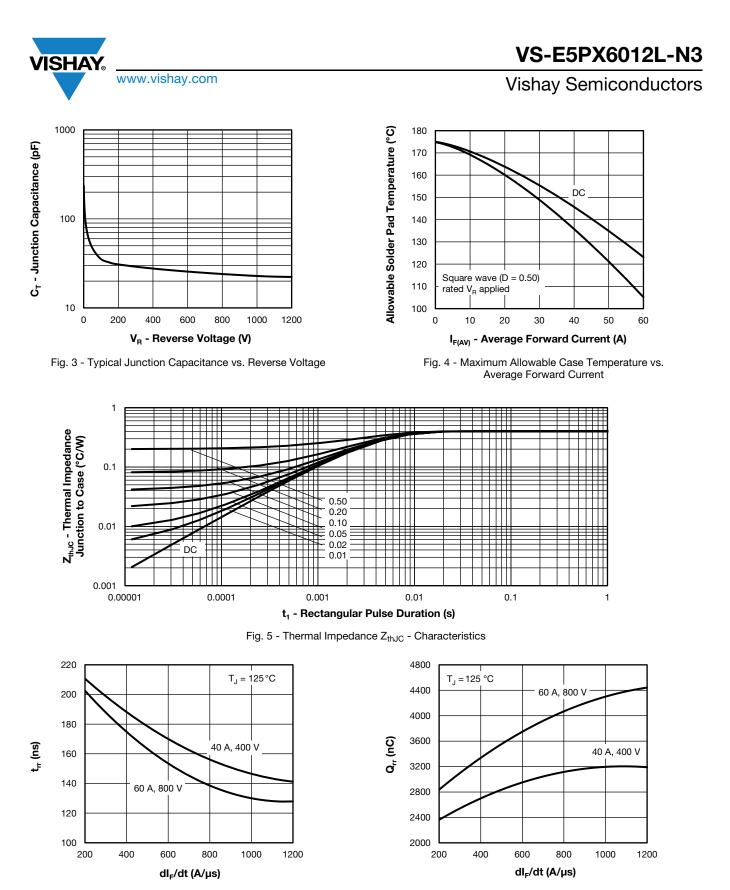


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

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Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

# VS-E5PX6012L-N3

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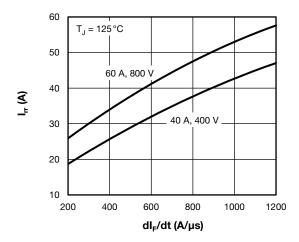


Fig. 8 - Typical Recovery Current vs. dl<sub>F</sub>/dt

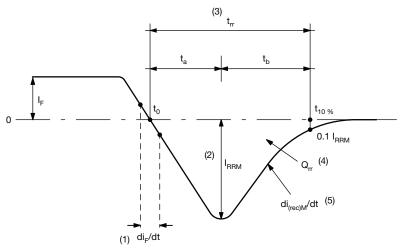


Fig. 9 - Reverse Recovery Waveform and Definitions

#### Notes

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- $^{(1)}~di_{F}/dt$  rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from  $t_0$ , crossing point of negative going I<sub>F</sub>, to point  $t_{10\%}$ , 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10}~\%$

$$Q_{rr} = \int_{t_0}^{t_{10}\%} I(t)dt$$

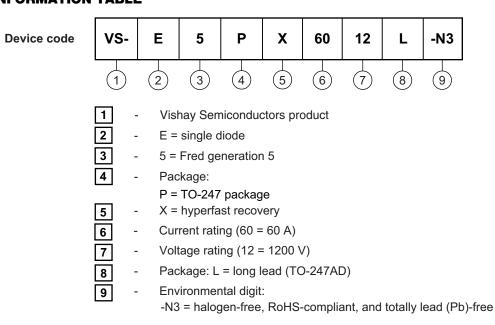
 $^{(5)}$  di\_{(rec)}M/dt - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

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ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-E5PX6012L-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95536						
Part marking information	www.vishay.com/doc?95648					
SPICE model	www.vishay.com/doc?96556					



**Vishay Semiconductors** 

**TO-247AD 2L** 

### **DIMENSIONS** in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDUL	MIN. MAX. MIN. MAX.	NOTES	NOTES .	STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES			
А	4.65	5.31	0.183	0.209			E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102			E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098			е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055			ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053			L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092			ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053				•		•		•

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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